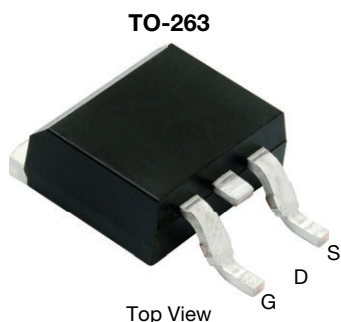




N-Channel 200 V (D-S) 175 °C MOSFET



FEATURES

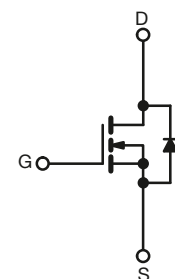
- ThunderFET® power MOSFET
- Low R_{DS} - Q_g figure-of-merit (FOM)
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- Power supplies
- DC/AC inverter
- DC/DC converter
- Solar micro inverter
- Motor drive switch



N-Channel MOSFET

PRODUCT SUMMARY

| | |
|--|--------|
| V_{DS} (V) | 200 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V | 0.0375 |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5$ V | 0.0422 |
| Q_g typ. (nC) | 21 |
| I_D (A) | 35.1 |
| Configuration | Single |

ORDERING INFORMATION

| | |
|---------------------------------|---------------|
| Package | TO-263 |
| Lead (Pb)-free and halogen-free | SUM90330E-GE3 |

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|---|----------------|----------------|-------------------|
| Drain-source voltage | V_{DS} | 200 | V |
| Gate-source voltage | V_{GS} | ± 20 | V |
| Continuous drain current | I_D | $T_C = 25$ °C | 35.1 |
| | | $T_C = 125$ °C | 20.3 |
| Pulsed drain current ($t = 100$ μ s) | I_{DM} | 70 | A |
| Continuous source-drain diode current | I_S | 12.5 | A |
| Single pulse avalanche current ^a | I_{AS} | 33 | mJ |
| Single pulse avalanche energy ^a | | | |
| Maximum power dissipation | P_D | $T_C = 25$ °C | 125 ^b |
| | | $T_C = 125$ °C | 41.7 ^b |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +175 | °C |
| Soldering recommendations (peak temperature) ^c | | 260 | |

THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | MAXIMUM | UNIT |
|--|------------|---------|------|
| Maximum junction-to-ambient (PCB mount) ^c | R_{thJA} | 40 | °C/W |
| Maximum junction-to-case (drain) | R_{thJC} | 1.2 | |

Notes

- Duty cycle ≤ 1 %
- See SOA curve for voltage derating
- When mounted on 1" square PCB (FR4 material)



| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|---|---------------|--|------|--------|--------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | 200 | - | - | V |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2 | - | 4 | V |
| Gate-source leakage | I_{GSS} | $V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$ | - | - | 250 | nA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$ | - | - | 1 | μA |
| | | $V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ | - | - | 150 | |
| | | $V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ | - | - | 5 | mA |
| On-state drain current ^a | $I_{D(on)}$ | $V_{DS} \geq 10\text{ V}$, $V_{GS} = 10\text{ V}$ | 20 | - | - | A |
| Drain-source on-state resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 12.2\text{ A}$ | - | 0.0312 | 0.0375 | Ω |
| | | $V_{GS} = 7.5\text{ V}$, $I_D = 11.5\text{ A}$ | - | 0.0337 | 0.0422 | |
| Forward transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}$, $I_D = 10\text{ A}$ | - | 28 | - | S |
| Dynamic ^b | | | | | | |
| Input capacitance | C_{iss} | $V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$ | - | 1172 | - | pF |
| Output capacitance | C_{oss} | | - | 150 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 11 | - | |
| Total gate charge | Q_g | $V_{DS} = 100\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 12.2\text{ A}$ | - | 21 | 32 | nC |
| Gate-source charge | Q_{gs} | | - | 6 | - | |
| Gate-drain charge | Q_{gd} | | - | 5.3 | - | |
| Gate resistance | R_g | $f = 1\text{ MHz}$ | 0.76 | 3.8 | 7.6 | Ω |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 100\text{ V}$, $R_L = 14.2\text{ }\Omega$, $I_D \cong 7\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$ | - | 12 | 24 | ns |
| Rise time | t_r | | - | 25 | 50 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 30 | 50 | |
| Fall time | t_f | | - | 22 | 44 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Pulse diode forward current ($t = 100\text{ }\mu\text{s}$) | I_{SM} | | - | - | 70 | A |
| Body diode voltage | V_{SD} | $I_F = 7\text{ A}$, $V_{GS} = 0\text{ V}$ | - | 0.8 | 1.5 | V |
| Body diode reverse recovery time | t_{rr} | $I_F = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ | - | 111 | 170 | ns |
| Body diode reverse recovery charge | Q_{rr} | | - | 0.51 | 1 | μC |
| Reverse recovery fall time | t_a | | - | 94 | - | ns |
| Reverse recovery rise time | t_b | | - | 17 | - | |
| Body diode peak reverse recovery charge | $I_{RM(REC)}$ | | - | 8.5 | 17 | A |

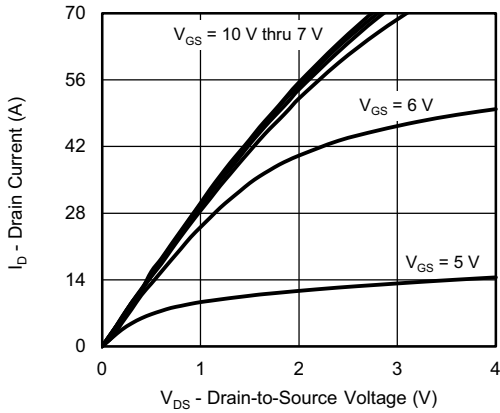
Notes

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production testing
- Independent of operating temperature

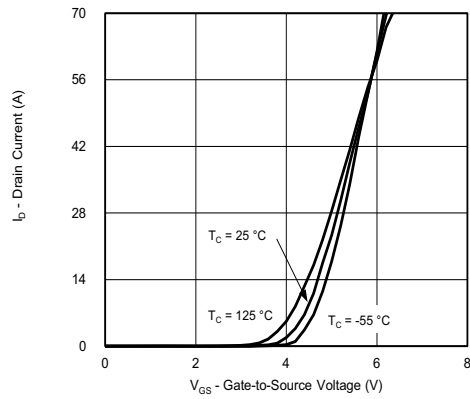
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



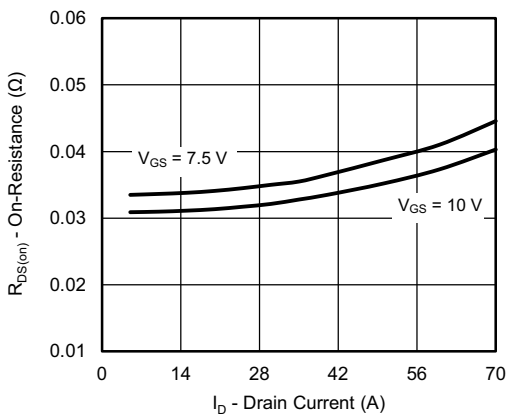
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



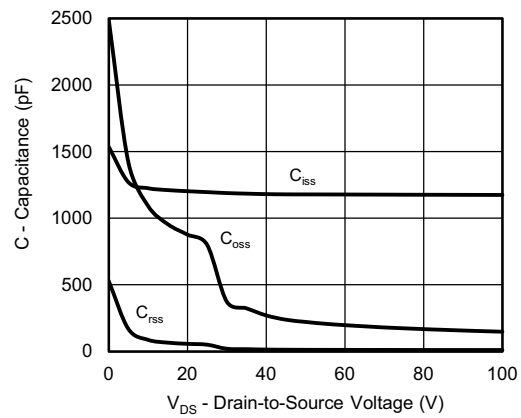
Output Characteristics



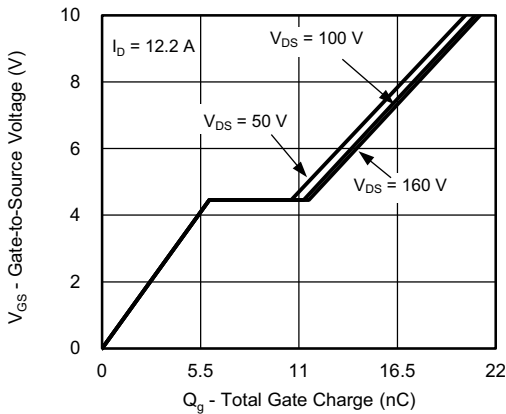
Transfer Characteristics



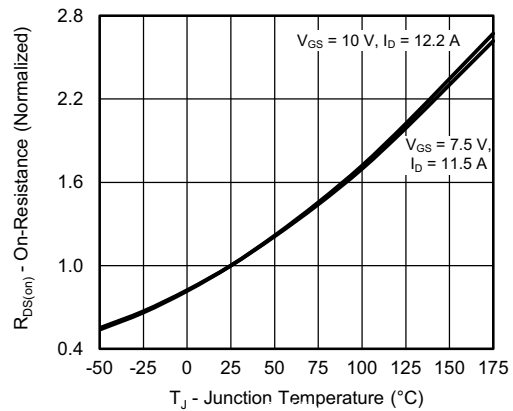
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



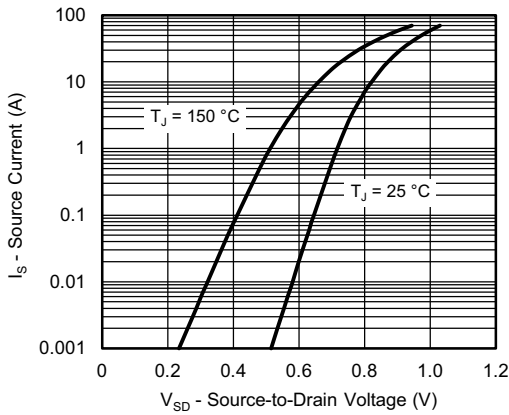
Gate Charge



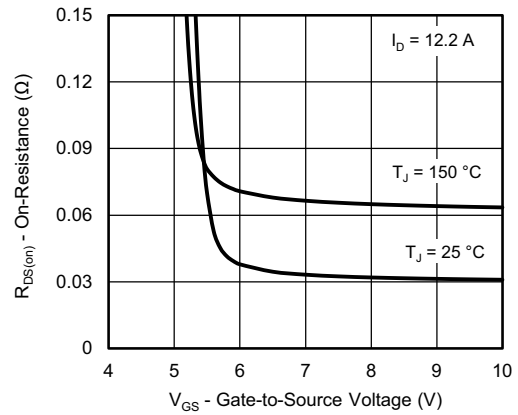
On-Resistance vs. Junction Temperature



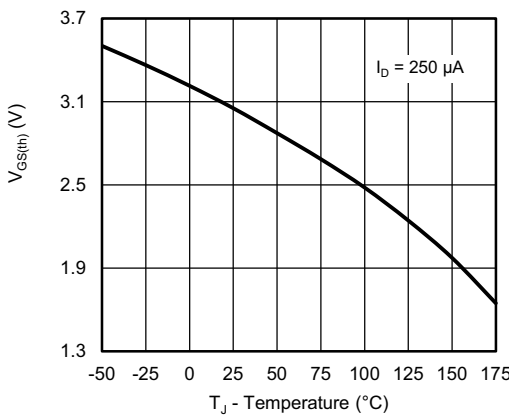
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



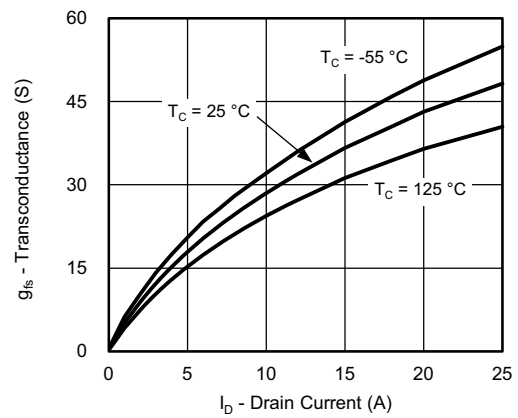
Source-Drain Diode Forward Voltage



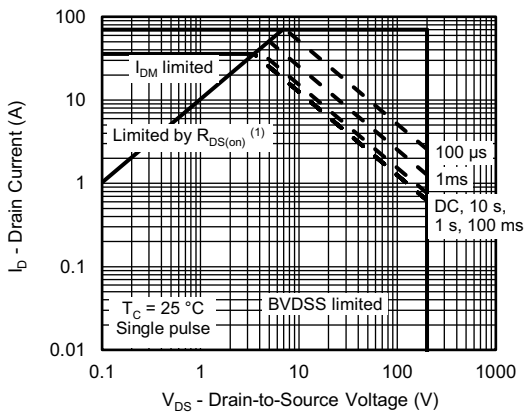
On-Resistance vs. Gate-to-Source Voltage



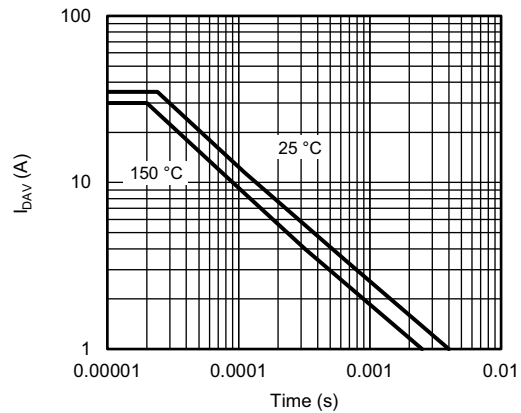
Threshold Voltage



Transconductance



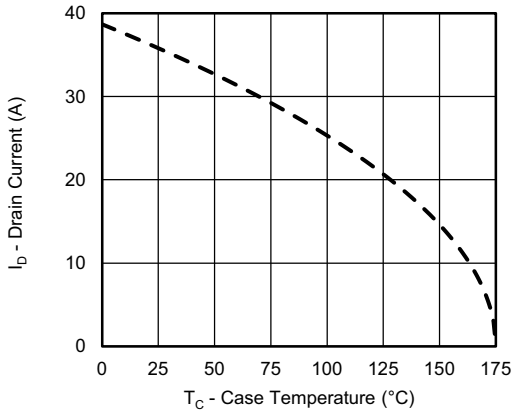
Safe Operating Area, Junction-to-Ambient



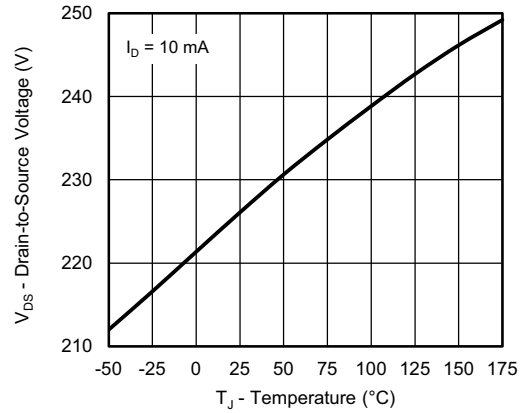
Avalanche vs. Time



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



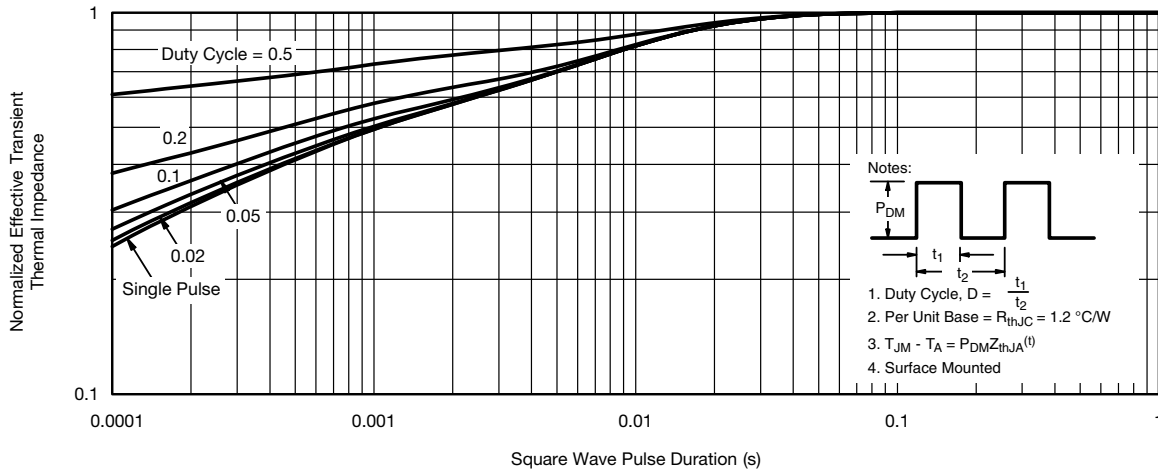
Current Derating ^a



Drain Source Breakdown vs. Junction Temperature

Note

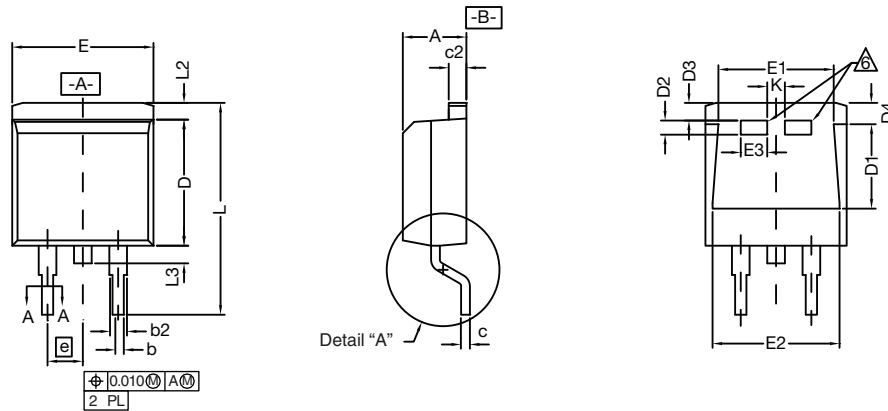
a. The power dissipation P_D is based on $T_J \text{ max.} = 25 \text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-263 (D²PAK): 3-LEAD



| DIM. | INCHES | | MILLIMETERS | | |
|---------------------------------|------------|-------|-------------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. | |
| A | 0.160 | 0.190 | 4.064 | 4.826 | |
| b | 0.020 | 0.039 | 0.508 | 0.990 | |
| b1 | 0.020 | 0.035 | 0.508 | 0.889 | |
| b2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| c* | Thin lead | 0.013 | 0.018 | 0.330 | 0.457 |
| | Thick lead | 0.023 | 0.028 | 0.584 | 0.711 |
| c1 | Thin lead | 0.013 | 0.017 | 0.330 | 0.431 |
| | Thick lead | 0.023 | 0.027 | 0.584 | 0.685 |
| c2 | 0.045 | 0.055 | 1.143 | 1.397 | |
| D | 0.340 | 0.380 | 8.636 | 9.652 | |
| D1 | 0.220 | 0.240 | 5.588 | 6.096 | |
| D2 | 0.038 | 0.042 | 0.965 | 1.067 | |
| D3 | 0.045 | 0.055 | 1.143 | 1.397 | |
| D4 | 0.044 | 0.052 | 1.118 | 1.321 | |
| E | 0.380 | 0.410 | 9.652 | 10.414 | |
| E1 | 0.245 | - | 6.223 | - | |
| E2 | 0.355 | 0.375 | 9.017 | 9.525 | |
| E3 | 0.072 | 0.078 | 1.829 | 1.981 | |
| e | 0.100 BSC | | 2.54 BSC | | |
| K | 0.045 | 0.055 | 1.143 | 1.397 | |
| L | 0.575 | 0.625 | 14.605 | 15.875 | |
| L1 | 0.090 | 0.110 | 2.286 | 2.794 | |
| L2 | 0.040 | 0.055 | 1.016 | 1.397 | |
| L3 | 0.050 | 0.070 | 1.270 | 1.778 | |
| L4 | 0.010 BSC | | 0.254 BSC | | |
| M | - | 0.002 | - | 0.050 | |
| ECN: T13-0707-Rev. K, 30-Sep-13 | | | | | |
| DWG: 5843 | | | | | |

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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